

Silicon NPN Power Transistors

2SC3310

DESCRIPTION

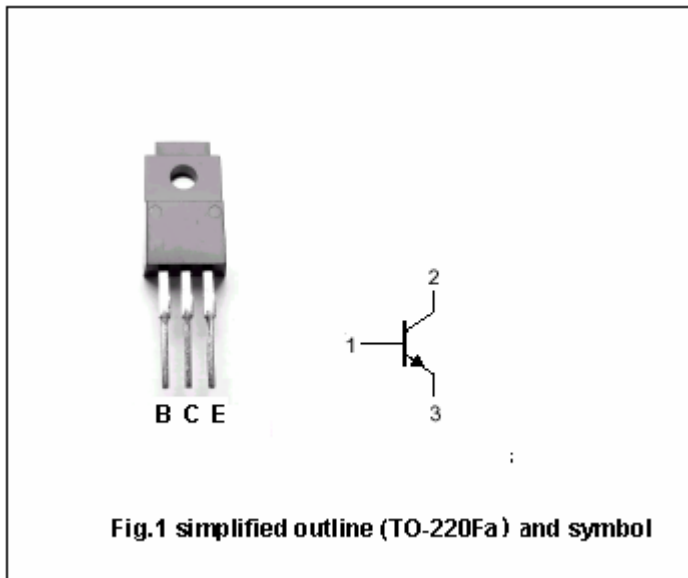
- With TO-220Fa package
- High collector breakdown voltage
- Excellent Switching times

APPLICATIONS

- Switching regulator
- High speed DC-DC converter
- High voltage switching

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current (DC)		5	A
I <sub>CM</sub>	Collector current (pulse)		7	A
I <sub>B</sub>	Base current (DC)		1	A
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25°C	2	W
		T <sub>C</sub> =25°C	30	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

## Silicon NPN Power Transistors

## 2SC3310

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA ; I <sub>E</sub> =0	500			V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	400			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =1A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =1A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =400V ; I <sub>E</sub> =0			100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V ; I <sub>C</sub> =0			1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =3A ; V <sub>CE</sub> =5V	12			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =5V	8			

## Switching times

T <sub>r</sub>	Rise time	I <sub>C</sub> =4A ; I <sub>B1</sub> =-I <sub>B2</sub> =0.4A V <sub>CC</sub> ≈200V ; R <sub>L</sub> =10Ω			1.0	μs
t <sub>s</sub>	Storage time				2.5	μs
t <sub>f</sub>	Fall time				1.0	μs

Silicon NPN Power Transistors

2SC3310

PACKAGE OUTLINE

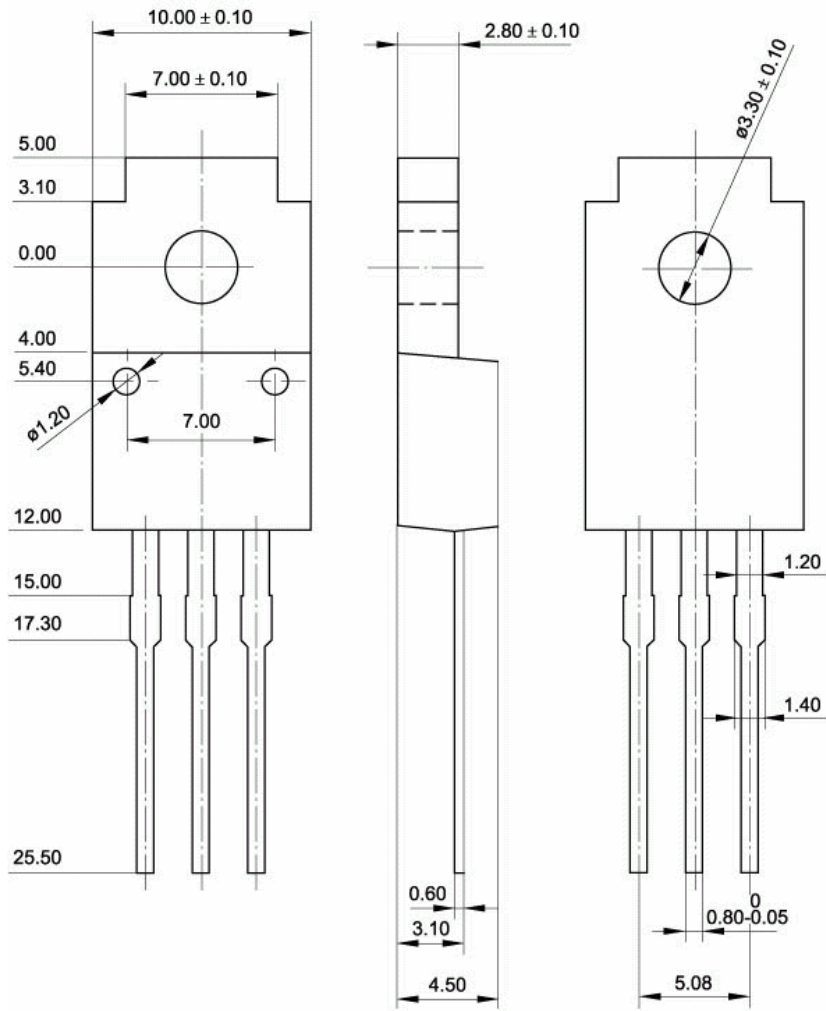


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)

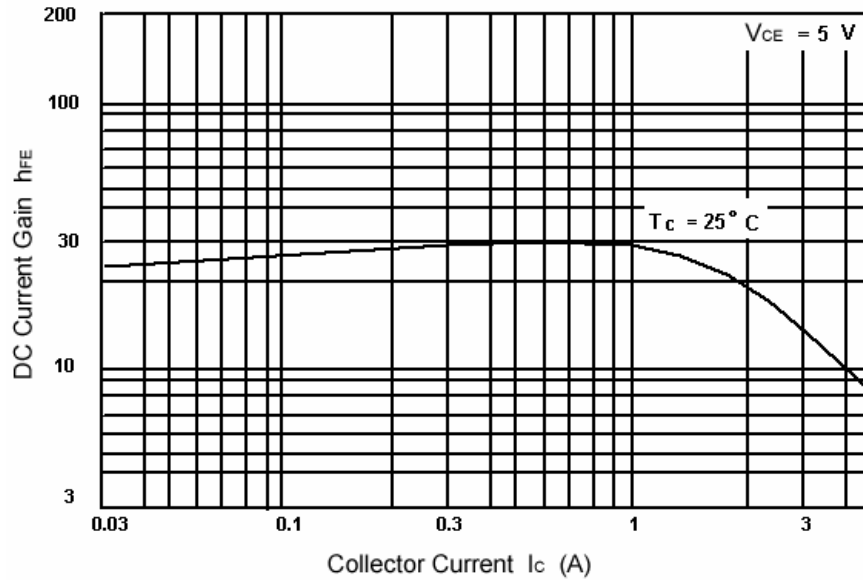


Fig.3 DC current Gain

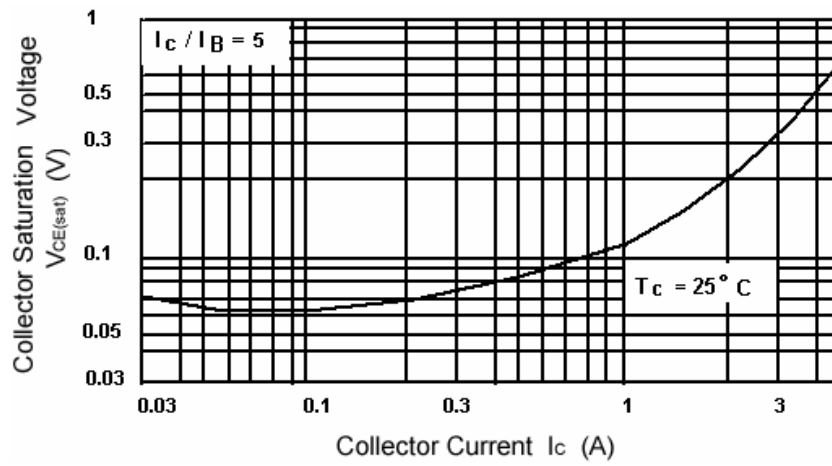


Fig.4 Collector-Emitter Saturation Voltage

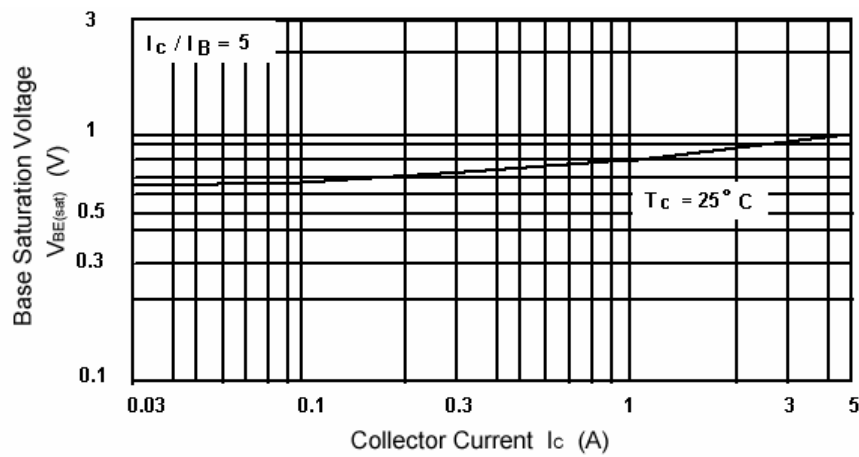


Fig.5 Base-Emitter Saturation Voltage

Silicon NPN Power Transistors

2SC3310

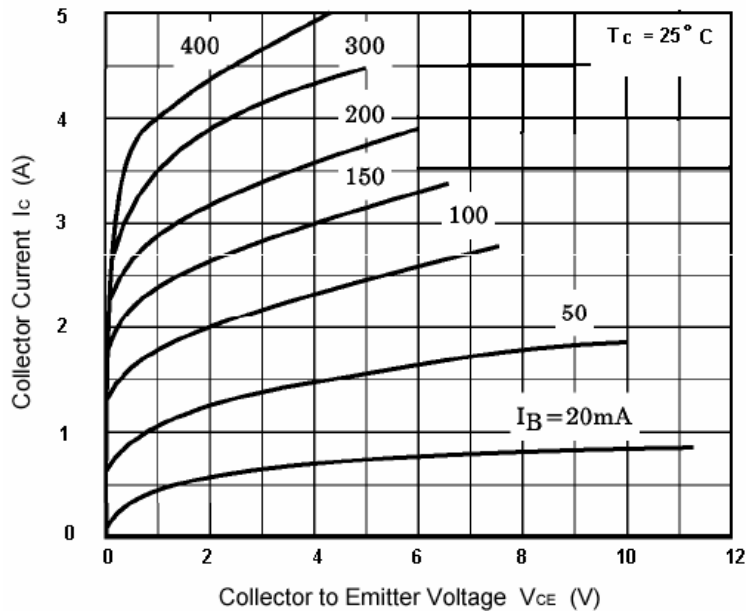


Fig.6 Static Characteristic

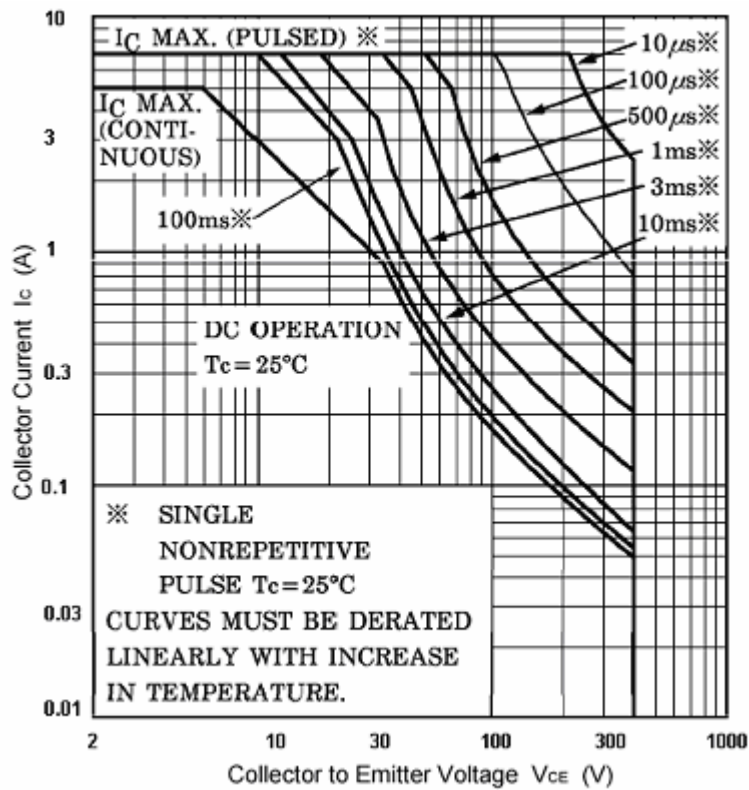


Fig.7 Safe Operating Area